What is claimed is;

1. An ion implantation equipment comprising

an ion sounce,

a mass sepalation means to extract so as to separate an ion beam having a specified mass from plurality of ion beams by giving a magnetic field so as to deflect said ion beams generated from an ion sounce,

a scanning means for scanning said ion beams by giving said magnetic field changing magnetic field strength thereof in time to said ion beam extracted by said mass sepalation means, and

an angle correction means for correcting a scan angle of said ion beam scanned by said scanning means in a scanning surface so as to irradiate corrected said ion beam into an implantation target.

2. An ion implantation equipment comprising

an ion sounce,

a mass sepalation means to extract so as to separate an ion beam having a specified mass from plurality of ion beams by giving a magnetic field so as to deflect said ion beams generated from an ion sounce,

a scan means for scanning the ion beam extracted by said mass isolation means by adding magnetic field changing a magnetic field strength in time, and

an angle correction means for correcting a scanning angle in a scanning surface of said ion beam by adding said magnetic field changing magnetic field strength thereof in

time to said ion beam scanned by said scanning means.

3. An ion implantation equipment as defined in claims 1 and 2, wherein

said scanning means for putting together a scanning surface of said ion beam with a deflection surfaceface of said ion beam deflected by said mass separation means.

4. An ion implantation equipment as defined in claim 2, wherein

said scanning means comprises an electromagnet for scanning to provide said magnetic field to said ion beam extracted by said mass separation means, a control signal generation means for said scanning to generate a control signal for said scanning, and a scanning electric current control means to change size in time of said electric current flowing into said electromagnet responding to said control signal for said scanning, and

said angle correction means comprises an electromagnet for angle correction to provided said magnetic field to said ion beam scanned by said scanning means, a control signal generating means for angle compensation to generate a control signal for said angle correction, and an angle correction electric current control means to change size in time of said electric current flowing into said electromagnet for said angle correction responding to said control signal for said angle correction.

5. An ion implantation equipment as defined in claim 2, wherein

said scanning means comprises an electromagnet for scanning to provide said magnetic field to said ion beam extracted by said mass separation means, a control signal generation means for said scanning to generate a control signal for said scanning, and a scanning electric current control means to change size in time of said electric current flowing into said electromagnet responding to said control signal for said scanning, and

said angle correction means comprises an electromagnet for angle correction to provided said magnetic field to said ion beam scanned by said scanning means, a control signal generating means for angle compensation to generate a control signal for said angle correction, a phase control means to move a phase of said control signal for said angle correction 180 degrees to said control signal for said scanning, and an angle correction electric current control means to change size in time of said electric current flowing into said electromagnet for said angle correction responding to said control signal for said angle correction being controlled said phase by said phase control means.

6. An ion implantation equipment as defined in claim 2, wherein

said scanning means comprises an electromagnet for scanning to provide said magnetic field to said ion beam extracted by said mass separation means, a control signal generation means for said scanning to generate a control signal for said scanning, and a scanning electric current

control means to change size in time of said electric current flowing into said electromagnet responding to said control signal for said scanning, and

said angle correction means comprises an electromagnet for angle correction to provided said magnetic field to said ion beam scanned by said scanning means, a control signal generating means for angle correction to generate said control signal for said angle correction 180 degrees to said control signal for said scanning, and an angle correction electric current control means to change size in time of said electric current flowing into said electromagnet for said angle correction responding to said control signal for said angle correction.

7. An ion implantation method comprising the steps of

giving a magnetic field so as to deflect said ion beams generated from an ion sounce,

extracting so as to separate an ion beam having a specified mass from plurality of ion beams,

scanning said ion beams by giving said magnetic field changing magnetic field strength thereof in time to said ion beam extracted, and

correcting a scanning angle of said ion beam scanned in a scanning surface so as to irradiate corrected said ion beam into an implantation target.

8. An ion implantation method comprising the steps of

giving a magnetic field so as to deflect said ion beams generated from an ion sounce,

extracting so as to separate an ion beam having a specified mass from plurality of ion beams ,

scanning the ion beam extracted by said mass isolation means by adding magnetic field changing a magnetic field strength in time, and

correcting a scanning angle in a scanning surface of said ion beam by adding said magnetic field changing magnetic field strength thereof in time to said ion beam scanned so as to irradiate corrected said ion beam into an implantation target.